

10V Drive Nch MOSFET

R5007ANJ

Structure

Silicon N-channel MOSFET

Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Wide SOA (safe operating area).
- 4) Gate-source voltage (VGSS) guaranteed to be ±30V.
- 5) Drive circuits can be simple.
- 6) Parallel use is easy.

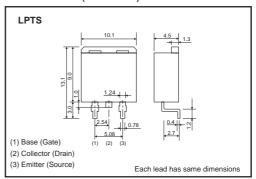
Applications

Switching

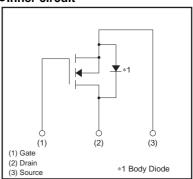
Packaging specifications

	Package	Taping
	Code	TL
Туре	Basic ordering unit (pieces)	1000
R5007	0	

●Dimensions (Unit: mm)



•Inner circuit



● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol		Limits	Unit	
Drain-source voltage	VDSS		500	V	
Gate-source voltage	Vgss		±30	V	
Drain current	Continuous	lo	*3	±7	А
Drain current	Pulsed	IDP	*1	±28	А
Source current	Continuous	Is	*3	7	А
(Body Diode)	Pulsed	Isp	*1	28	А
Avalanche Current	las	*2	3.5	А	
Avalanche Energy	Eas	*2	3.5	mJ	
Total power dissipatio	Po		40	W	
Channel temperature	Tch		150	°C	
Range of storage tem	Tstg		-55 to +150	°C	

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to case	Rth(ch-c)	3.13	°C/W

^{*1} Pw≤10 μ s, Duty cycle≤1% *2 L \leftrightarrows 500 μ H, V $_{DD}$ =50V, R $_{G}$ =25 Ω , Starting, Tch=25°C *3 Limited only by maximum tempterature allowed

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	Igss	-	_	±100	nA	Vgs=±30V, Vps=0V	
Drain-source breakdown voltage	V(BR)DSS	500	_	_	V	ID=1mA, VGS=0V	
Zero gate voltage drain current	IDSS	_	_	100	μΑ	Vps=500V, Vgs=0V	
Gate threshold voltage	VGS(th)	2.5	-	4.5	V	Vos=10V, Io=1mA	
Static drain-source on-state resistance	RDS(on)*	_	0.8	1.05	Ω	In=3.5A, Vgs=10V	
Forward transfer admittance	Yfs *	2.5	_	_	S	ID=3.5A, VDS=10V	
Input capacitance	Ciss	_	500	_	pF	Vps=25V	
Output capacitance	Coss	_	300	_	pF	V _G s=0V	
Reverse transfer capacitance	Crss	_	23	_	pF	f=1MHz	
Turn-on delay time	td(on) *	_	20	_	ns	ID=3.5A, VDD≒250V	
Rise time	tr *	_	22	_	ns	Vgs=10V	
Turn-off delay time	td(off) *	_	50	_	ns	RL=71.4Ω	
Fall time	t _f *	_	25	_	ns	R _G =10Ω	
Total gate charge	Qg *	_	13	_	nC	V _{DD} ≒250V	
Gate-source charge	Qgs *	_	3.5	_	nC	I _D =7A V _G s=10V	
Gate-drain charge	Q _{gd} *	_	5.5	_	nC	$R_L=35.7\Omega / R_G=10\Omega$	

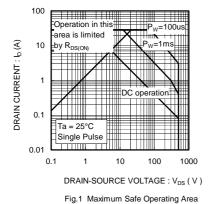
^{*} Pulsed

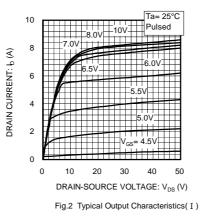
●Body diode characteristics (Source-drain) (Ta=25°C)

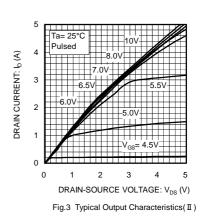
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	_	_	1.5	V	I _S = 7A, V _{GS} =0V

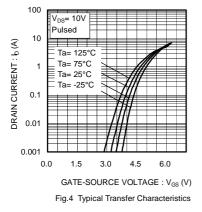
^{*} Pulsed

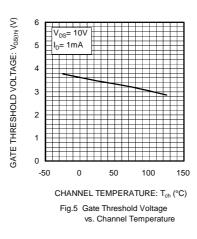
•Electrical characteristic curves

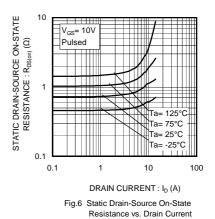


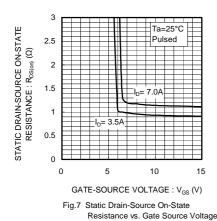


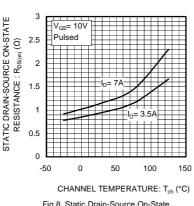












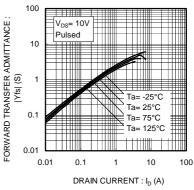
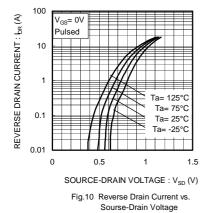
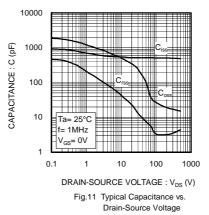
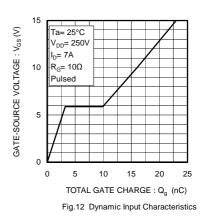


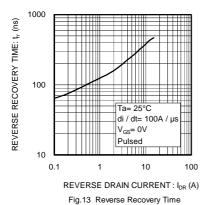
Fig.9 Forward Transfer Admittance vs. Drain Current

R5007ANJ Data Sheet









vs.Reverse Drain Current

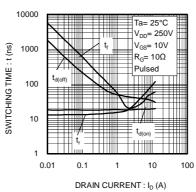


Fig.14 Switching Characteristics

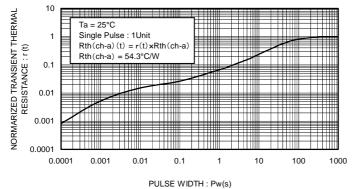


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

R5007ANJ Data Sheet

•Switching characteristics measurement circuit

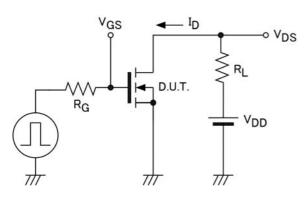


Fig.1 Switching time measurement circuit

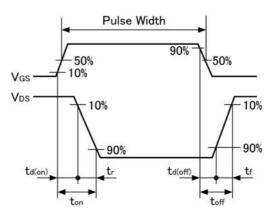


Fig.2 Switching waveforms

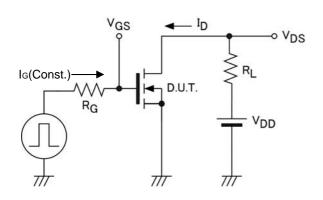


Fig.3 Gate charge measurement circuit

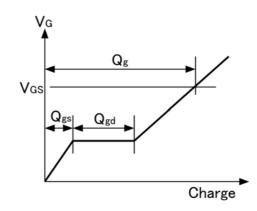


Fig.4 Gate charge waveform

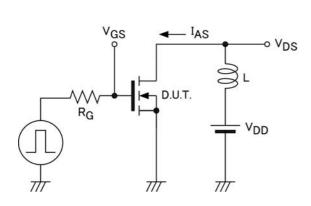


Fig.5 Avalanche measurement circuit

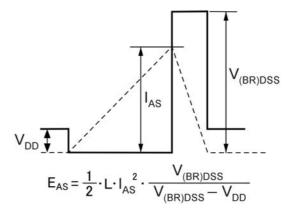


Fig.6 Avalanche waveform

Notes

No copying or reproduction of this document, in part or in whole, is permitted without the consent of ROHM CO.,LTD.

The content specified herein is subject to change for improvement without notice.

The content specified herein is for the purpose of introducing ROHM's products (hereinafter "Products"). If you wish to use any such Product, please be sure to refer to the specifications, which can be obtained from ROHM upon request.

Examples of application circuits, circuit constants and any other information contained herein illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.

Great care was taken in ensuring the accuracy of the information specified in this document. However, should you incur any damage arising from any inaccuracy or misprint of such information, ROHM shall bear no responsibility for such damage.

The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM and other parties. ROHM shall bear no responsibility whatsoever for any dispute arising from the use of such technical information.

The Products specified in this document are intended to be used with general-use electronic equipment or devices (such as audio visual equipment, office-automation equipment, communication devices, electronic appliances and amusement devices).

The Products are not designed to be radiation tolerant.

While ROHM always makes efforts to enhance the quality and reliability of its Products, a Product may fail or malfunction for a variety of reasons.

Please be sure to implement in your equipment using the Products safety measures to guard against the possibility of physical injury, fire or any other damage caused in the event of the failure of any Product, such as derating, redundancy, fire control and fail-safe designs. ROHM shall bear no responsibility whatsoever for your use of any Product outside of the prescribed scope or not in accordance with the instruction manual.

The Products are not designed or manufactured to be used with any equipment, device or system which requires an extremely high level of reliability the failure or malfunction of which may result in a direct threat to human life or create a risk of human injury (such as a medical instrument, transportation equipment, aerospace machinery, nuclear-reactor controller, fuel-controller or other safety device). ROHM shall bear no responsibility in any way for use of any of the Products for the above special purposes. If a Product is intended to be used for any such special purpose, please contact a ROHM sales representative before purchasing.

If you intend to export or ship overseas any Product or technology specified herein that may be controlled under the Foreign Exchange and the Foreign Trade Law, you will be required to obtain a license or permit under the Law.

Thank you for your accessing to ROHM product informations.

More detail product informations and catalogs are available, please contact your nearest sales office.

ROHM Customer Support System

THE AMERICAS / EUROPE / ASIA / JAPAN

www.rohm.com

Contact us : webmaster @ rohm.co.jp

Copyright © 2009 ROHM Co.,Ltd.

ROHM Co., Ltd. 21 Saiin Mizosaki-cho, Ukyo-ku, Kyoto 615-8585, Japan

TEL:+81-75-311-2121 FAX:+81-75-315-0172



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by ROHM manufacturer:

Other Similar products are found below:

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW216A-TL-2W FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3